

Chip Termination 200 Watts, 50Ω



Features:

- RoHS Compliant
- 200 Watts
- DC 2.2 GHz
- AIN Ceramic
- Non Nichrome Resistive Element
- Low VSWR
- 100% Tested

Description:

The A200N50X4 is high performance Aluminum Nitride (AIN) Chip termination intended as a low cost alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for termination circulators and for use in power combiners. The termination is also RoHS compliant!

General Specifications:

Resistive Element	Thick film
Substrate	AIN Ceramic

Terminal Finish Matte Tin over Nickel Barrier **Operating Temperature** -50 to +200°C (see de rating chart)

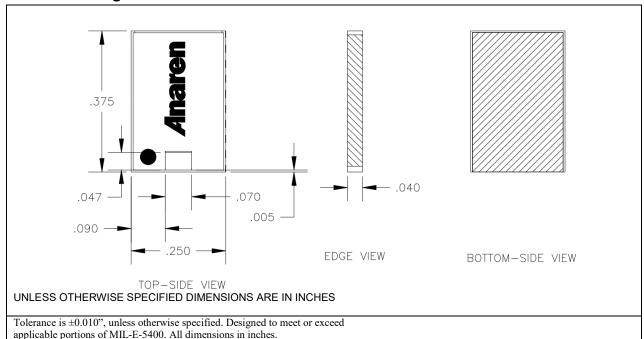
Electrical Specifications:

Resistance Value: 50 Ohms, ± 2%
Power: 200 Watts
Frequency Range: DC - 2.2 GHz

Return Loss > 20 dB DC – 2.2 GHz

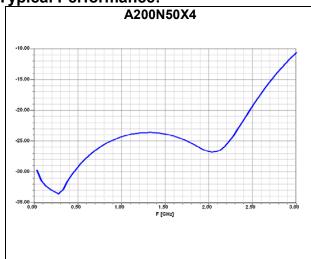
Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. Specifications subject to change.

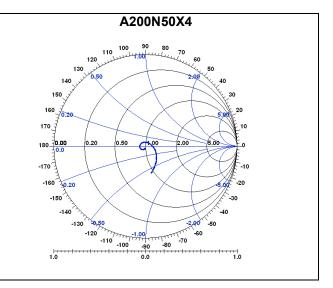
Outline Drawing:



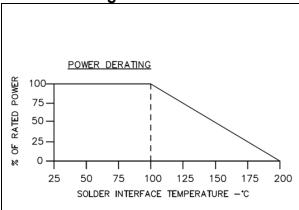


Typical Performance:



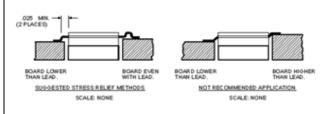


Power De-rating:



*Actual performance could be limited by the solder properties of the application

Mounting Footprint:



SUGGESTED MOUNTING PROCEDURE

- MAKE SURE THAT THE DEVICES ARE MOUNTED ON FLAT SURFACES (.001" UNDER THE DEVICE) TO OPTIMIZE THE HEAT TRANSFER.
- POSITION DEVICE ON MOUNTING SURFACE AND SOLDER IN PLACE USING AN APPROPRIATE SOLDER.
- SOLDER LEADS IN PLACE USING AN APPROPRIATE SOLDER TYPE WITH A CONTROLLED TEMPERATURE IRON.

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